

MOSFETs Silicon Carbide N-Channel MOS

TW030N120C

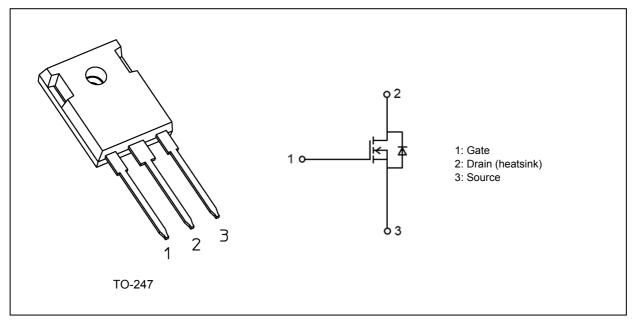
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage: $V_{DSS} = 1200 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 30 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: $V_{th} = 3.0$ to 5.0 V ($V_{DS} = 10$ V, $I_D = 13$ mA)
- (6) Recommended gate source drive voltage: $V_{GS_on} = 18 \text{ V}$, $V_{GS_off} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| | Characteristics | Symbol | Rating | Unit |
|------------------------|----------------------------|------------------|------------|-------|
| Drain-source voltage | | V _{DSS} | 1200 | V |
| Gate-source voltage | | V _{GSS} | +25/-10 | |
| Drain current (DC) | (T _c = 25 °C) | I _D | 60 | Α |
| Drain current (DC) | (T _c = 100°C) | I _D | 42 | |
| Drain current (pulsed) | (T _c = 25 °C) | I _{DP} | 166 |] |
| Drain current (pulsed) | (T _c = 100°C) | I _{DP} | 125 |] |
| Power dissipation | (T _c = 25°C) | P _D | 249 | W |
| Channel temperature | | T _{ch} | 175 | °C |
| Storage temperature | | T _{stg} | -55 to 175 | |
| Mounting torque | | TOR | 0.8 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.602 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 50 | |

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

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6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|---------|----------------------|---|------|------|------|------|
| Gate leakage current | | I _{GSS} | V _{GS} = +25/-10 V, V _{DS} = 0 V | _ | _ | ±0.1 | μΑ |
| Drain cut-off current | | I _{DSS} | V _{DS} = 1200 V, V _{GS} = 0 V | _ | 1 | 20 | |
| | | | T _a = 150 °C, V _{DS} = 1200 V, V _{GS} = 0 V | | 8 | ı | |
| Drain-source breakdown voltage | | V _{(BR)DSS} | $I_D = 4$ mA, $V_{GS} = 0$ V | 1200 | _ | _ | V |
| Gate threshold voltage (| Note 2) | V_{th} | V _{DS} = 10 V, I _D = 13 mA | 3.0 | _ | 5.0 | |
| Drain-source on-resistance | | R _{DS(ON)} | V _{GS} = 18 V, I _D = 30 A | _ | 30 | 40 | mΩ |
| | | | T _a = 150 °C, V _{GS} = 18 V, I _D = 30 A | _ | 43 | | |

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|--------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 800 V, V _{GS} = 0 V, | _ | 2925 | _ | pF |
| Reverse transfer capacitance | C _{rss} | f = 100 kHz | _ | 4.3 | _ | |
| Output capacitance | C _{oss} |] | _ | 147 | _ | |
| Effective output capacitance (energy related) | C _{o(er)} | | _ | 175 | _ | |
| Effective output capacitance (time related) | C _{o(tr)} | | _ | 266 | _ | |
| Output charge | Q _{oss} |] | _ | 213 | _ | nC |
| C _{oss} stored energy | E _{oss} |] | _ | 56 | _ | μJ |
| Gate resistance | r _g | V _{DS} = OPEN, f = 1 MHz | _ | 2.2 | _ | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 53 | _ | ns |
| Switching time (turn-on time) | t _{on} |] | _ | 87 | _ | |
| Switching time (fall time) | t _f |] | _ | 49 | _ | |
| Switching time (turn-off time) | t _{off} | 1 | _ | 100 | _ | ns |

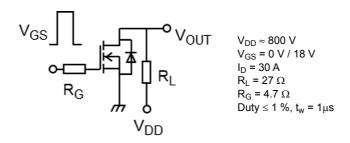


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 800 \text{ V}, V_{GS} = 18 \text{ V}, I_{D} = 30 \text{ A}$ | _ | 82 | _ | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 29 | _ | |
| Gate-drain charge | Q _{gd} | | _ | 13 | _ | |



6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|----------|------------------|--|-----|-------|-------|------|
| Reverse drain current (DC) | (Note 3) | I _{DR} | T _c = 25 °C, V _{GS} = -5 V | _ | _ | 50 | Α |
| | | | T _c = 100 °C, V _{GS} = -5 V | _ | _ | 33 | |
| | | | T _c = 25 °C, V _{GS} = 18 V | _ | _ | 60 | |
| | | | T _c = 100 °C, V _{GS} = 18 V | _ | _ | 42 | |
| Reverse drain current | (Note 3) | I _{DRP} | $T_c = 25 ^{\circ}\text{C}, V_{GS} = -5 ^{\circ}\text{V}$ | _ | _ | 166 | |
| (pulsed) | | | T _c = 100 °C, V _{GS} = -5 V | _ | _ | 56 | |
| | | | T _c = 25 °C, V _{GS} = 18 V | _ | _ | 166 | |
| | | | T _c = 100 °C, V _{GS} = 18 V | _ | _ | 125 | |
| Diode forward voltage | | V _{DSF} | I _{DR} = 16 A, V _{GS} = -5 V | _ | -1.35 | -1.80 | V |
| | | | T _a = 150 °C, I _{DR} = 16 A, V _{GS} = -5 V | _ | -1.70 | | |
| Reverse recovery time | | t _{rr} | I _{DR} = 20 A, V _{GS} = 0 V, | _ | 55 | _ | ns |
| Reverse recovery charge | | Q _{rr} | $V_{DD} = 800 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$ | _ | 358 | _ | nC |
| Peak reverse recovery current | | I _{rr} | | _ | 13 | | Α |

Note 3: Ensure that the channel temperature does not exceed 175 °C.

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7. Marking (Note)

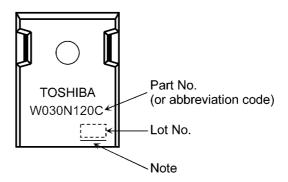


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

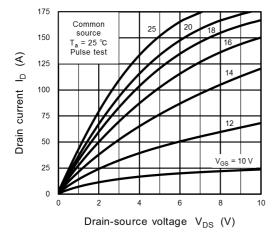


Fig. 8.1 I_D - V_{DS}

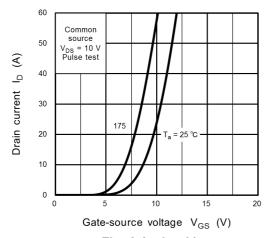


Fig. 8.3 ID - VGS

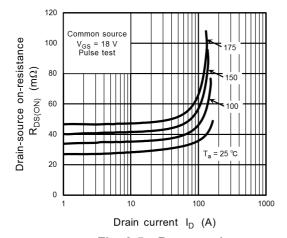


Fig. 8.5 $R_{DS(ON)}$ - I_D

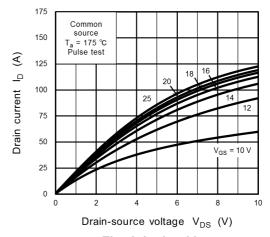


Fig. 8.2 I_D - V_{DS}

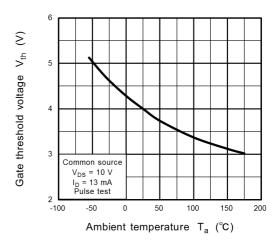


Fig. 8.4 V_{th} - T_a

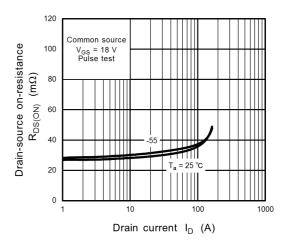


Fig. 8.6 R_{DS(ON)} - I_D



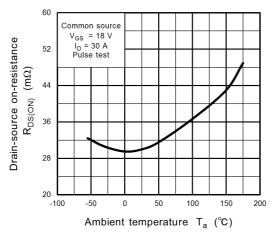


Fig. 8.7 R_{DS(ON)} - T_a

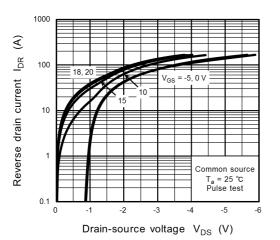


Fig. 8.9 IDR - VDS

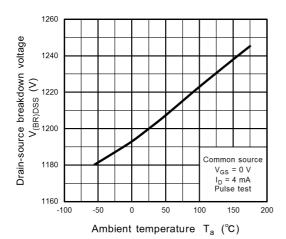


Fig. 8.11 V_{DSS} - T_a

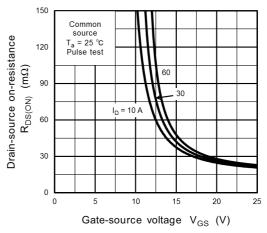


Fig. 8.8 R_{DS(ON)} - V_{GS}

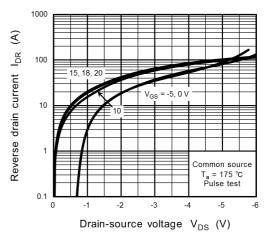


Fig. 8.10 I_{DR} - V_{DS}

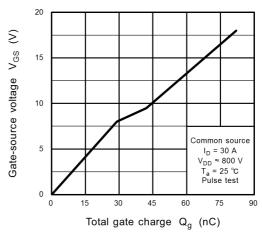
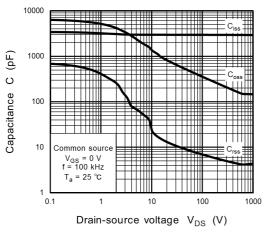


Fig. 8.12 Dynamic Input Characteristics





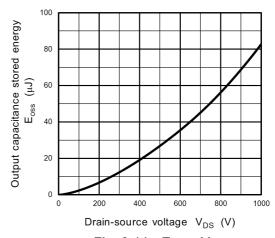


Fig. 8.13 C - V_{DS}

Fig. 8.14 E_{oss} - V_{DS}

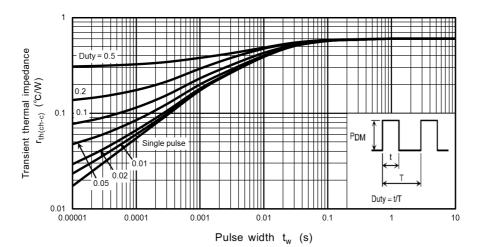
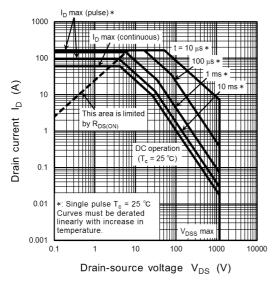


Fig. 8.15 $r_{th(ch-c)} - t_w$ (Guaranteed Maximum)



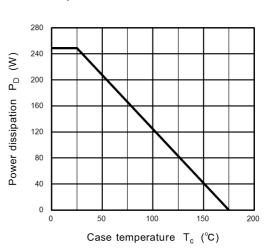


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

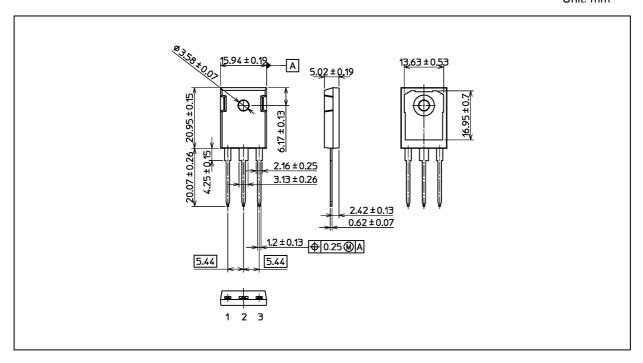
Fig. 8.17 P_D - T_c (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

| Package Name(s) |
|------------------|
| TOSHIBA: 2-16L1A |
| Nickname: TO-247 |



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